IN THE SPECIFICATION:

Please amend the Abstract of the Disclosure on page 31 as follows:

The present invention is generally directed to ~~doping methods for~~ a fully-depleted SOI device structure. ~~structures, and a device comprising such resulting doped regions.~~ In one illustrative embodiment, the device comprises first, second and third doped regions formed in the bulk substrate, wherein the dopant concentration level in the doped regions is greater than the dopant concentration in the bulk substrate. The first doped region is substantially aligned with the gate electrode of the device, while the second and third doped regions are vertically spaced apart from the first doped region. ~~a transistor formed above a silicon-on-insulator substrate comprised of a bulk substrate, a buried oxide layer and an active layer, the transistor being comprised of a gate electrode, the bulk substrate being doped with a dopant material at a first concentration level. The device further comprises a first doped region formed in the bulk substrate, the first doped region being doped with a dopant material that is the same type as the bulk substrate dopant material, wherein the concentration level of dopant material in the first doped region is greater than the first dopant concentration level in the bulk substrate, the first doped region being substantially aligned with the gate electrode.~~